ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D=12V R_L=33	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3k	ALL	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	-	MAX.	15	mA
		-		25	
I_H	I_T=100mA		MAX.	15	mA
dV/dt	V_D=540V Gate Open T_j=110		MIN.	100	V s
(dV/dt)c	(dI/dt)c=1.8A/ms, T_j=110		MIN.	2.5	9 V
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25		TYP.	1	s
t_{off}				12	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM}=5A t_p=380 s	T_j=25	1.7	V
V_{TO}	Threshold voltage	T_j=125	0.94	V
R_D	Dynamic resistance	T_j=125	124	P
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=125	0.4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	15	/W
$R_{th(j-a)}$	junction to ambient (AC)	150	/W

ORDERING INFORMATION

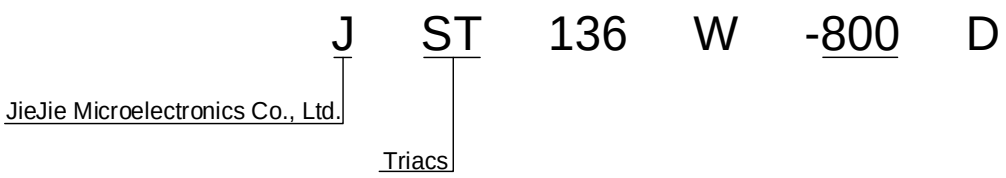


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

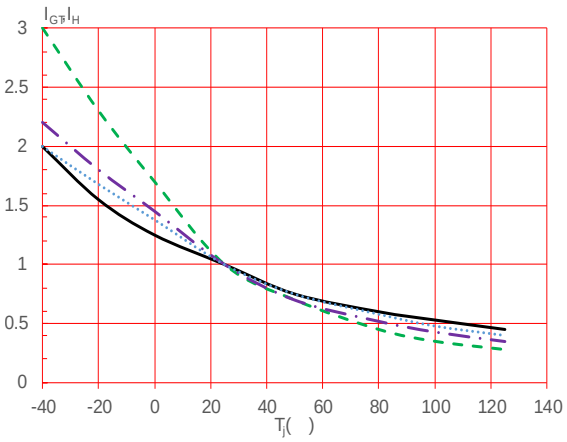
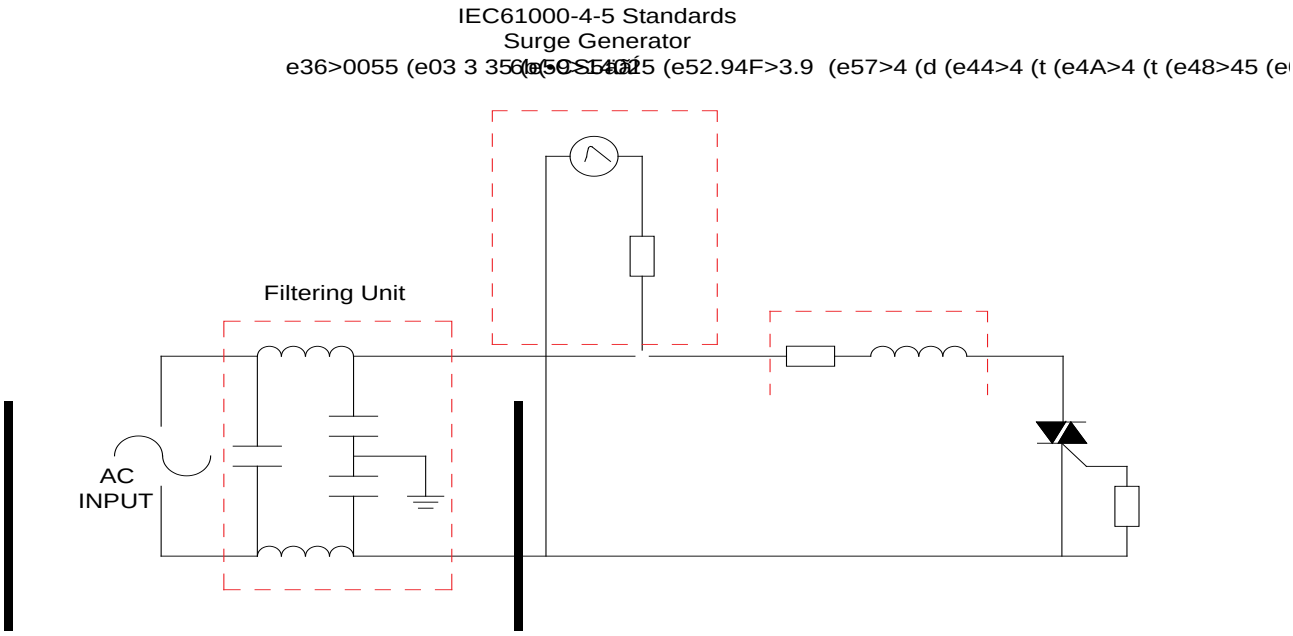


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



	IGT(mA)	Package	Base qty. (pcs)	
[redacted]				

PACKAGE MECHANICAL DATA